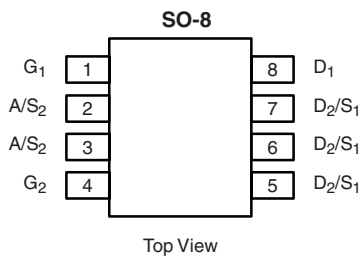




Dual N-Channel 30-V (D-S) MOSFET with Schottky Diode

PRODUCT SUMMARY				
	V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)	Q _g (Typ.)
Channel-1	30	0.0185 at V _{GS} = 10 V	6.8	7.8
		0.0225 at V _{GS} = 4.5 V	6.0	
Channel-2		0.0115 at V _{GS} = 10 V	11.4	11.6
		0.016 at V _{GS} = 4.5 V	9.5	

SCHOTTKY PRODUCT SUMMARY		
V _{DS} (V)	V _{SD} (V) Diode Forward Voltage	I _F (A)
30	0.50 V at 1.0 A	2.0



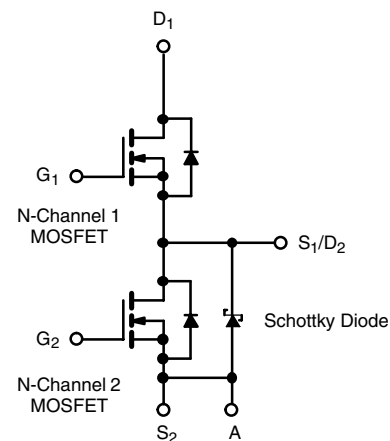
Ordering Information: Si4816BDY-T1-E3 (Lead (Pb)-free)
Si4816BDY-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

- Halogen-free According to IEC 61249-2-21 Available
- LITTLE FOOT® Plus Power MOSFET
- 100 % R_g Tested



RoHS
COMPLIANT
HALOGEN
FREE
Available



ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted							
Parameter	Symbol	Channel-1		Channel-2		Unit	
		10 s	Steady State	10 s	Steady State		
Drain-Source Voltage	V _{DS}	30				V	
Gate-Source Voltage	V _{GS}	20					
Continuous Drain Current (T _J = 150 °C) ^a	I _D	T _A = 25 °C	6.8	5.8	11.4	8.2	A
		T _A = 70 °C	5.5	4.6	9.0	6.5	
Pulsed Drain Current	I _{DM}	30		40		mJ	
Continuous Source Current (Diode Conduction) ^a	I _S	1	0.9	2.2	1.15		
Single Pulse Avalanche Current	I _{AS}	L = 0.1 mH	10		20		
Avalanche Energy			E _{AS}	5		20	
Maximum Power Dissipation ^a	P _D	T _A = 25 °C	1.4	1.0	2.4	1.25	W
		T _A = 70 °C	0.9	0.64	1.5	0.8	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150				°C	

THERMAL RESISTANCE RATINGS									
Parameter	Symbol	Channel-1		Channel-2		Schottky		Unit	
		Typ.	Max.	Typ.	Max.	Typ.	Max.		
Maximum Junction-to-Ambient ^a	R _{thJA}	t ≤ 10 s	72	90	43	53	48	60	°C/W
		Steady State	100	125	82	100	80	100	
Maximum Junction-to-Foot (Drain)	R _{thJF}	51	63	25	30	28	35		

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

MOSFET SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted							
Parameter	Symbol	Test Conditions		Min.	Typ. ^a	Max.	Unit
Static							
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	Ch-1	1.0		3.0	V
			Ch-2	1.0		3.0	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = 20\text{ V}$	Ch-1			100	nA
			Ch-2			100	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$	Ch-1			1	μA
			Ch-2			100	
		$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, T_J = 85\text{ }^\circ\text{C}$	Ch-1			15	
			Ch-2			2000	
On-State Drain Current ^b	$I_{D(on)}$	$V_{DS} = 5\text{ V}, V_{GS} = 10\text{ V}$	Ch-1	20			A
			Ch-2	30			
Drain-Source On-State Resistance ^b	$R_{DS(on)}$		Ch-1		0.0155	0.0185	Ω
			Ch-2		0.0093	0.0115	
			Ch-1		0.0185	0.0225	
			Ch-2		0.013	0.016	
Forward Transconductance ^b	g_{fs}		Ch-1		30		S
			Ch-2		31		
Diode Forward Voltage ^b	V_{SD}	$I_S = 1\text{ A}, V_{GS} = 0\text{ V}$	Ch-1		0.73	1.1	V
			Ch-2		0.47	0.5	
Dynamic^a							
Total Gate Charge	Q_g	Channel-1 $V_{DS} = 15\text{ V}, V_{GS} = 5\text{ V}, I_D = 6.8\text{ A}$	Ch-1		7.8	10	nC
			Ch-2		11.6	18	
Gate-Source Charge	Q_{gs}	Channel-2 $V_{DS} = 15\text{ V}, V_{GS} = 5\text{ V}, I_D = -11.4\text{ A}$	Ch-1		2.9		
			Ch-2		4.8		
Gate-Drain Charge	Q_{gd}		Ch-1		2.3		
			Ch-2		3.7		
Gate Resistance	R_g		Ch-1	1.5	3.0	4.5	Ω
			Ch-2	0.9	1.8	2.7	
Turn-On Delay Time	$t_{d(on)}$	Channel-1 $V_{DD} = 15\text{ V}, R_L = 15\text{ }\Omega$ $I_D \cong 1\text{ A}, V_{GEN} = 10\text{ V}, R_g = 6\text{ }\Omega$ Channel-2 $V_{DD} = 15\text{ V}, R_L = 15\text{ }\Omega$ $I_D \cong 1\text{ A}, V_{GEN} = 10\text{ V}, R_g = 6\text{ }\Omega$	Ch-1		11	17	ns
Rise Time	t_r		Ch-1		9	15	
			Ch-2		9	15	
Turn-Off Delay Time	$t_{d(off)}$		Ch-1		24	40	
			Ch-2		31	50	
Fall Time	t_f		Ch-1		9	15	
			Ch-2		11	17	
Source-Drain Reverse Recovery Time	t_{rr}		$I_F = 1.3\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}$	Ch-1		20	
		$I_F = 2.2\text{ A}, dI/dt = 100\text{ }\mu\text{A}/\mu\text{s}$	Ch-2		25	40	

Notes:

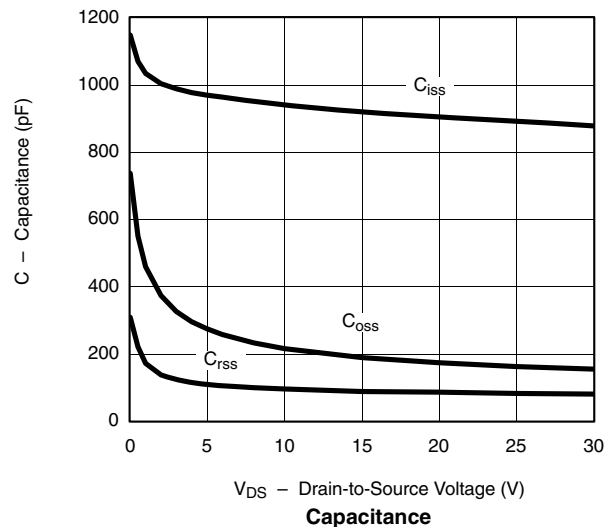
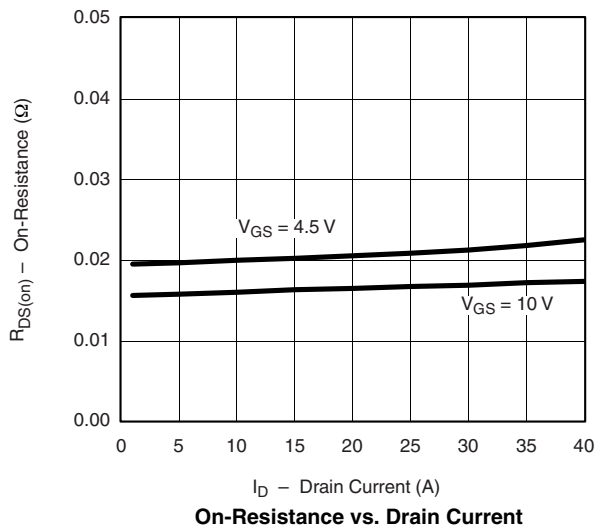
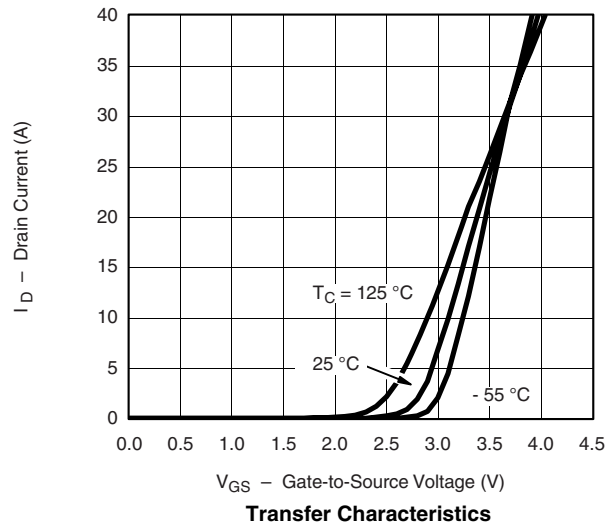
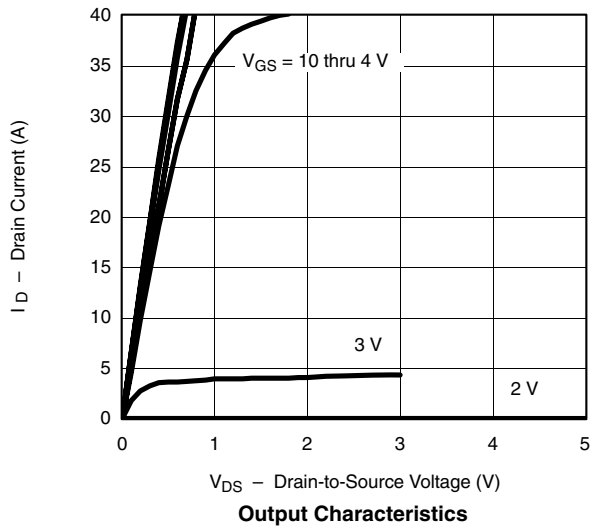
- a. Guaranteed by design, not subject to production testing.
b. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.



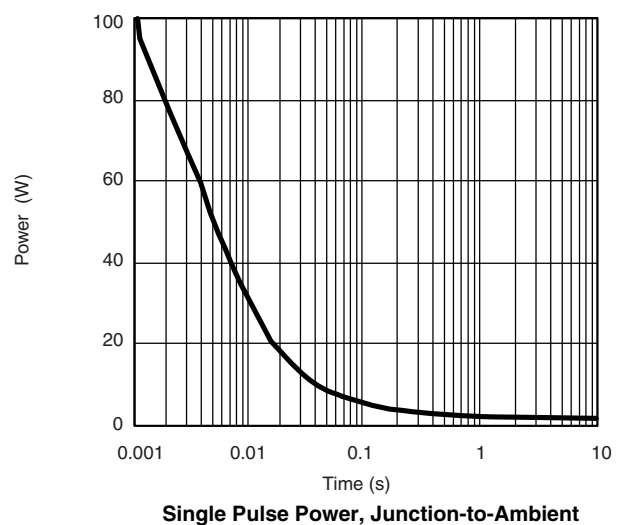
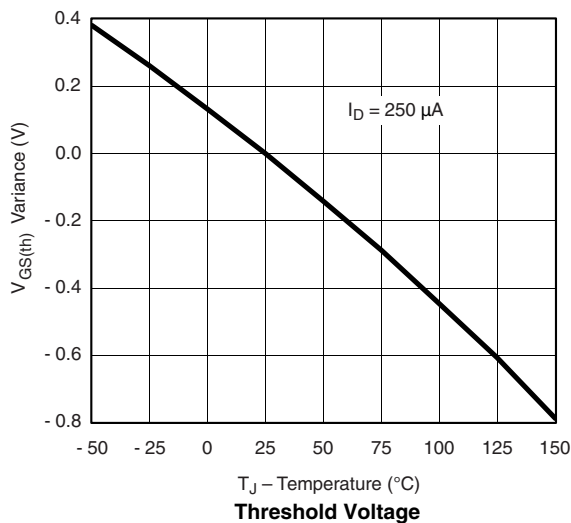
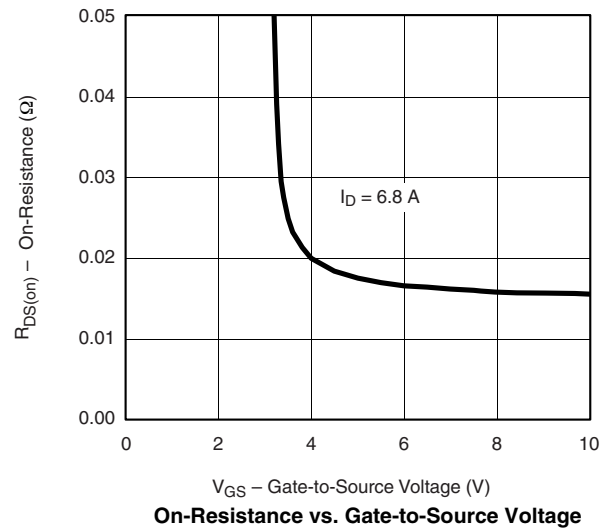
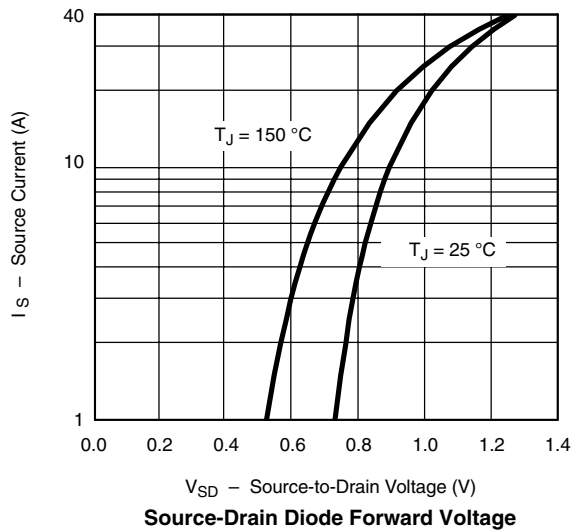
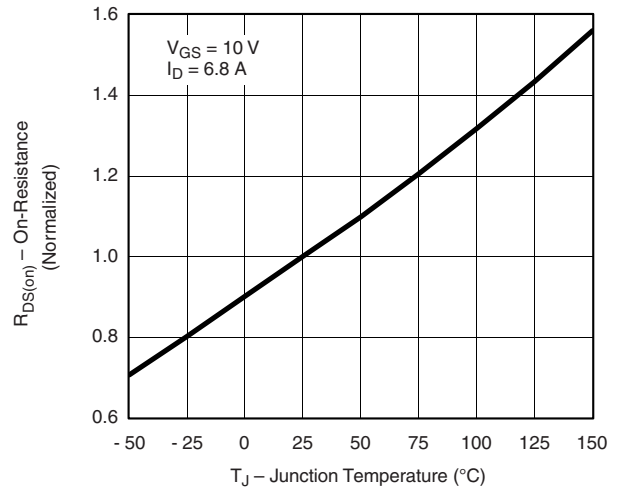
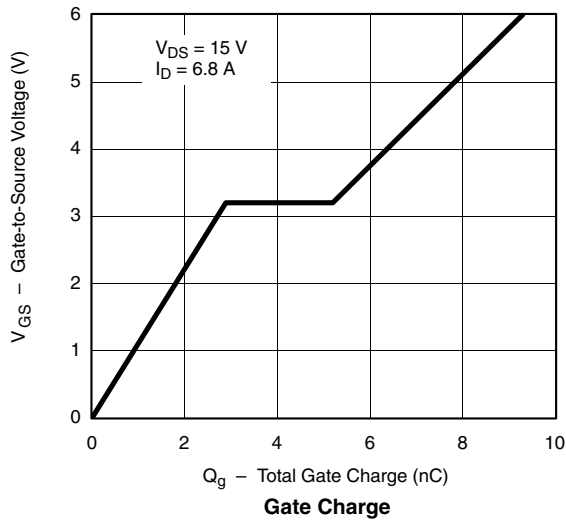
SCHOTTKY SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Forward Voltage Drop	V_F	$I_F = 1.0\text{ A}$		0.47	0.50	V
		$I_F = 1.0\text{ A}, T_J = 125\text{ }^\circ\text{C}$		0.36	0.42	
Maximum Reverse Leakage Current	I_{rm}	$V_R = 30\text{ V}$		0.004	0.100	mA
		$V_R = 30\text{ V}, T_J = 100\text{ }^\circ\text{C}$		0.7	10	
		$V_R = -30\text{ V}, T_J = 125\text{ }^\circ\text{C}$		3.0	20	
Junction Capacitance	C_T	$V_R = 10\text{ V}$		50		pF

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

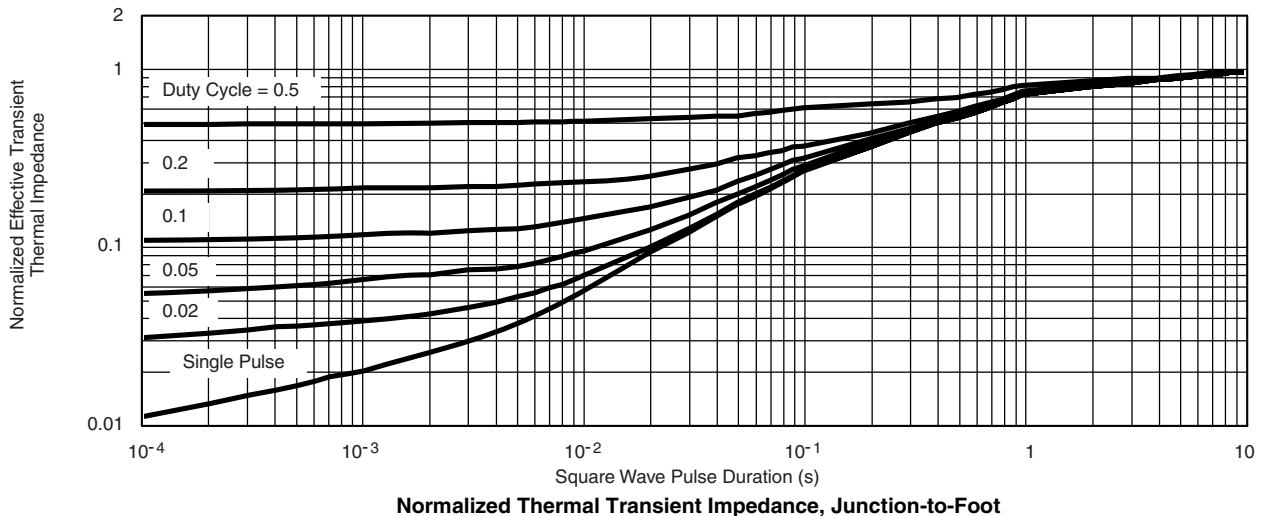
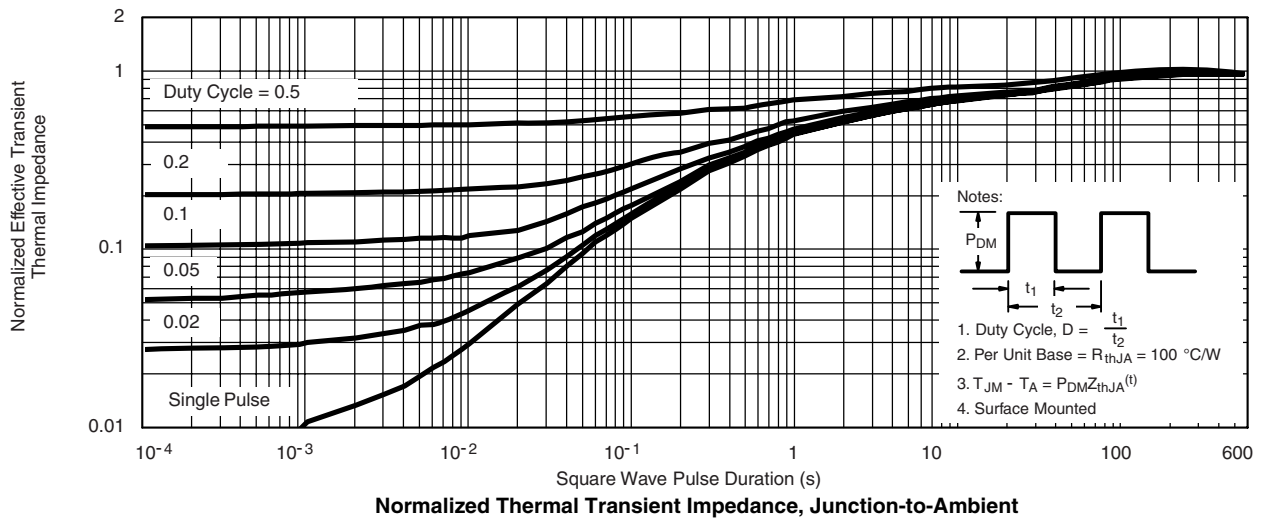
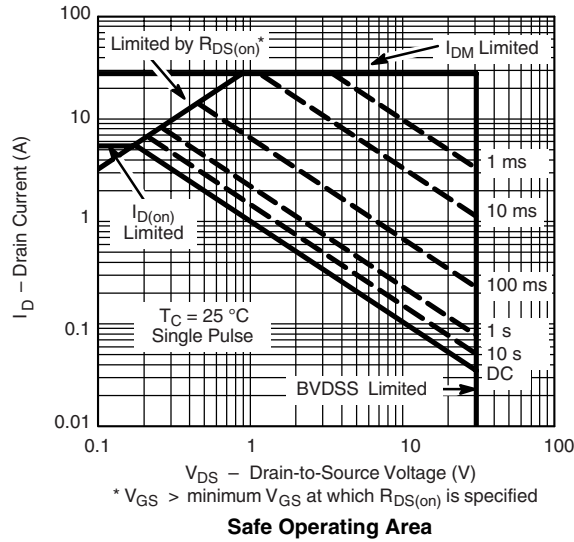
CHANNEL-1 TYPICAL CHARACTERISTICS $25\text{ }^\circ\text{C}$, unless otherwise noted



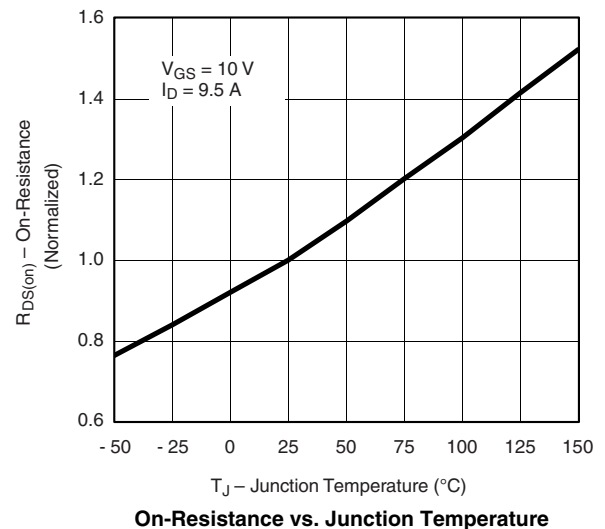
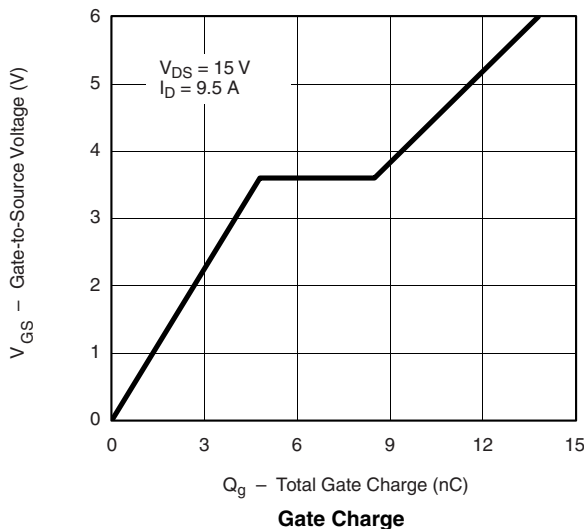
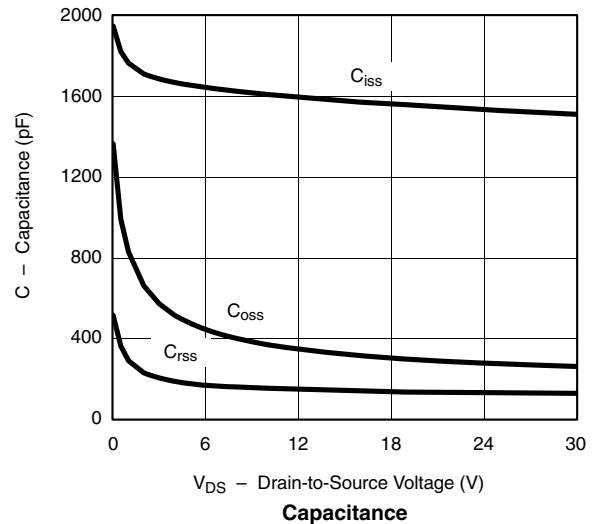
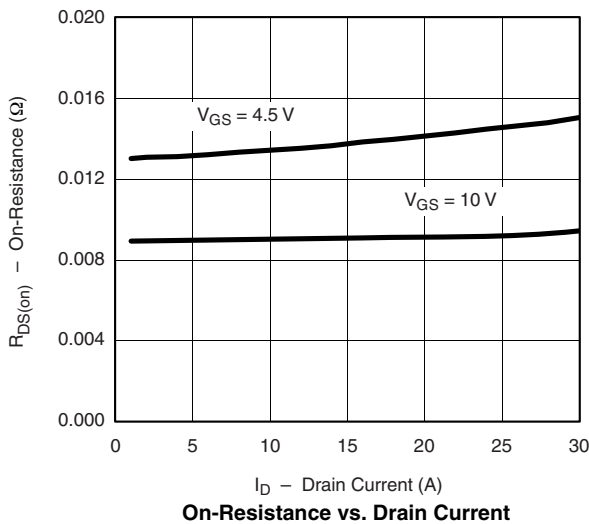
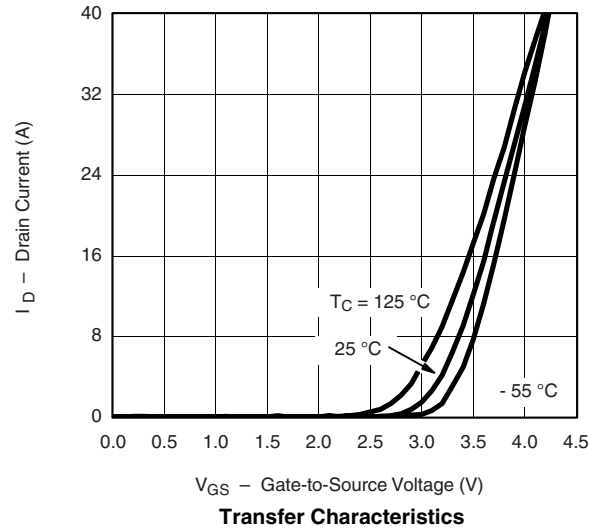
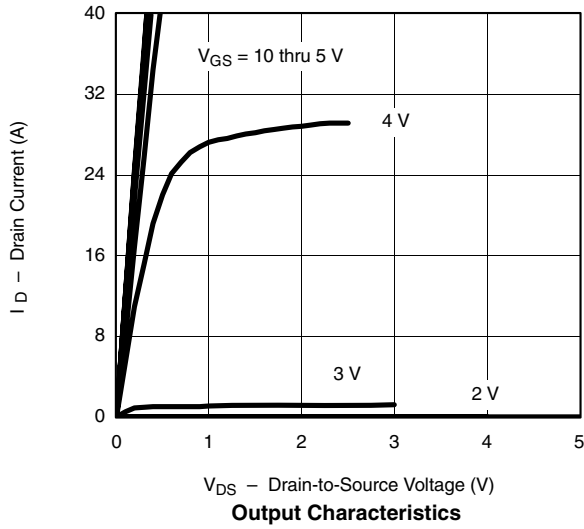
CHANNEL-1 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



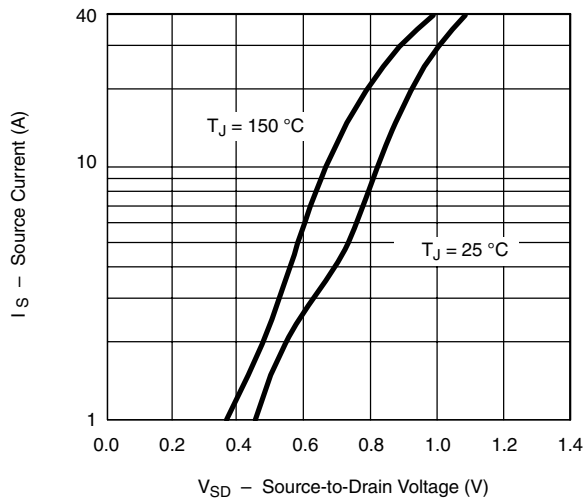
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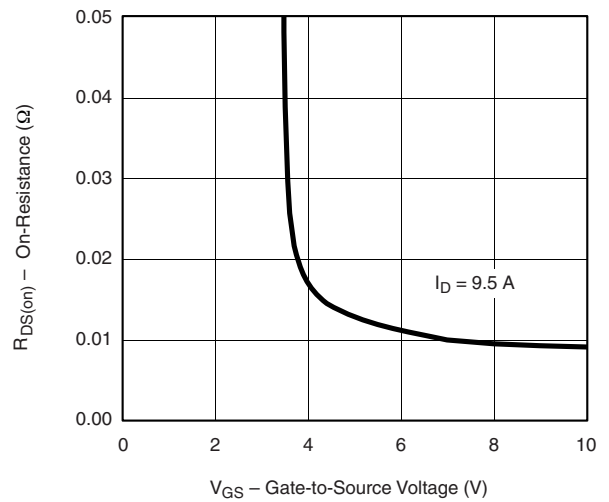
CHANNEL-2 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



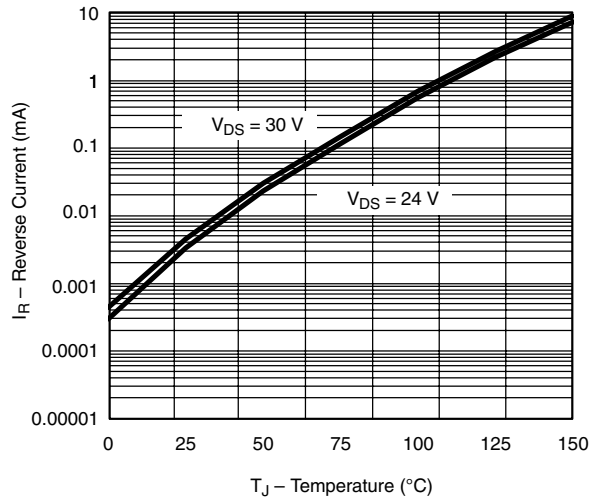
CHANNEL-2 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



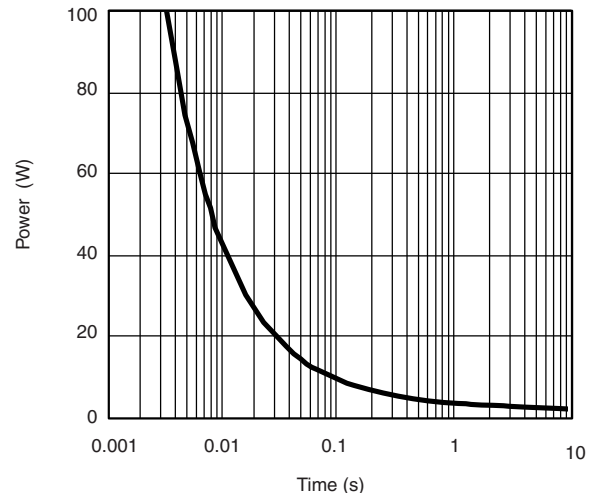
Source-Drain Diode Forward Voltage



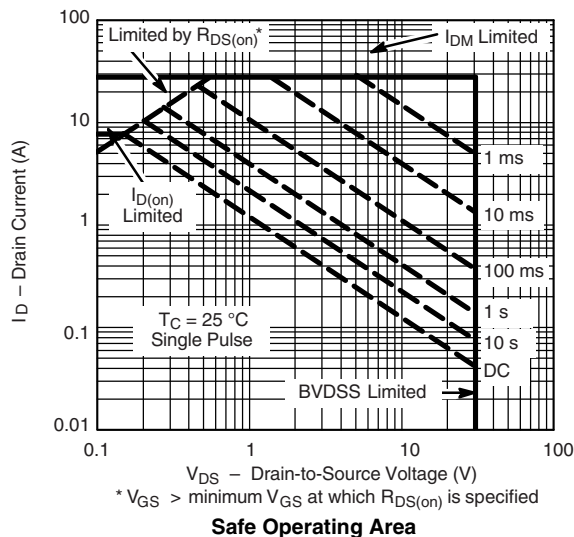
On-Resistance vs. Gate-to-Source Voltage



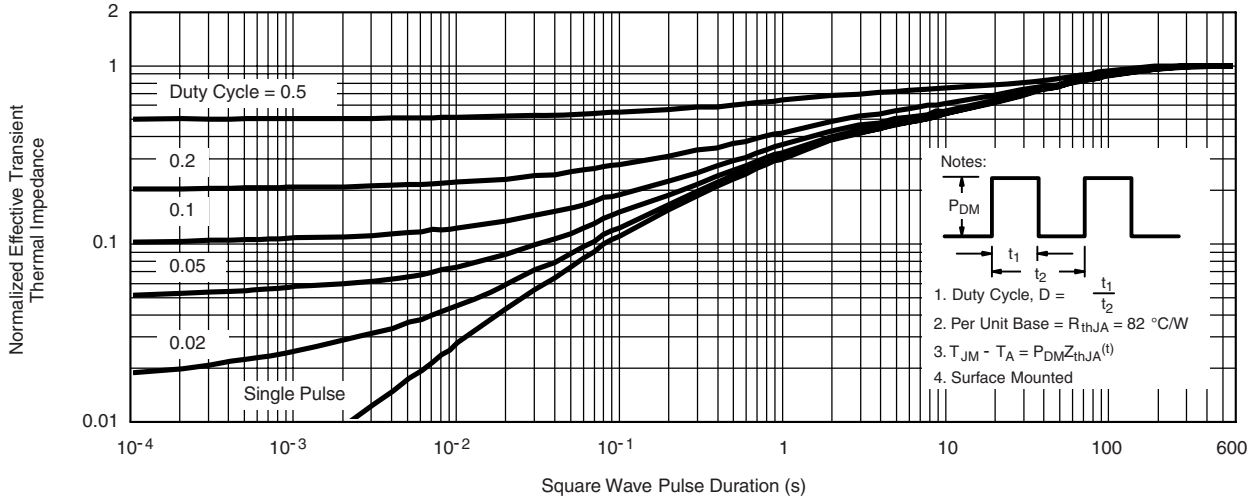
Reverse Current vs. Junction Temperature



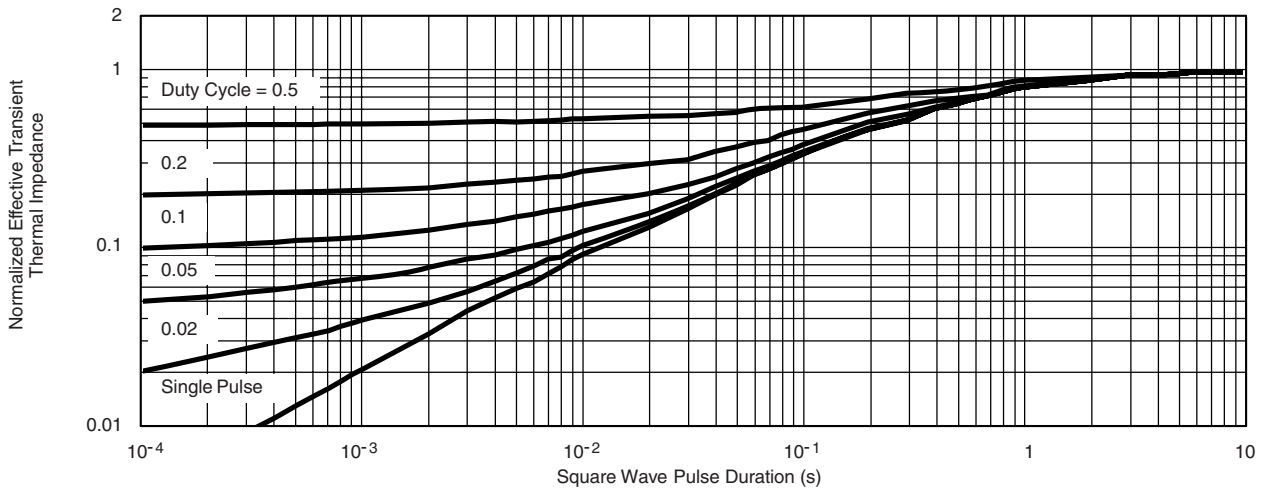
Single Pulse Power, Junction-to-Ambient



CHANNEL-2 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

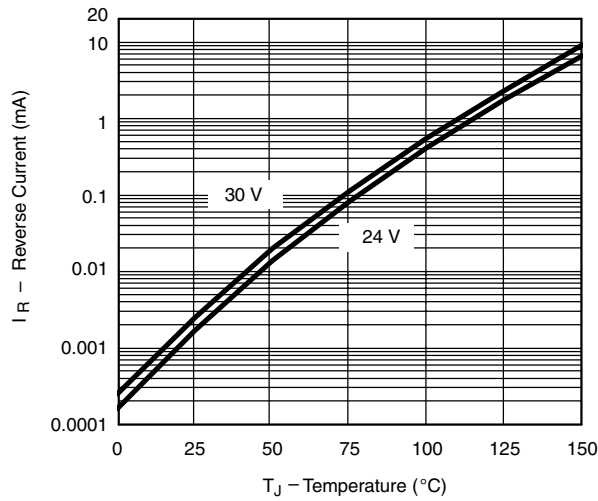


Normalized Thermal Transient Impedance, Junction-to-Ambient

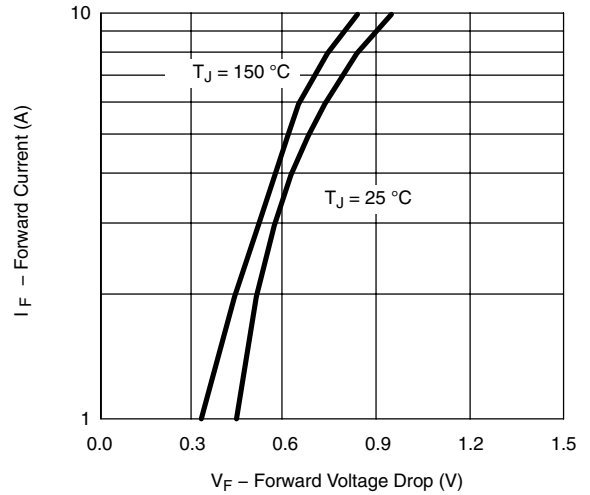


Normalized Thermal Transient Impedance, Junction-to-Foot

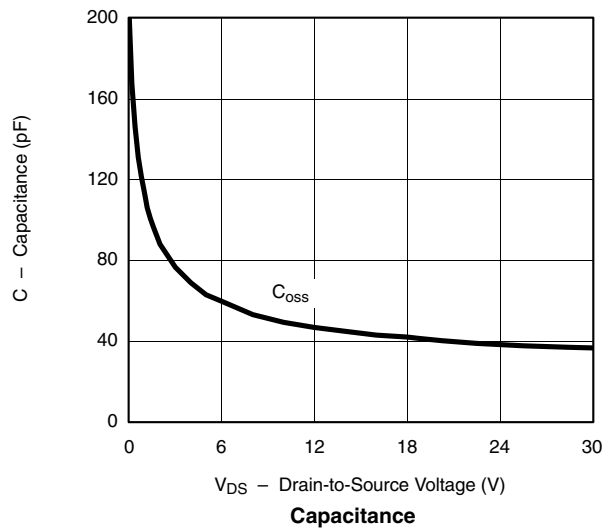
SCHOTTKY TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Reverse Current vs. Junction Temperature



Forward Voltage Drop

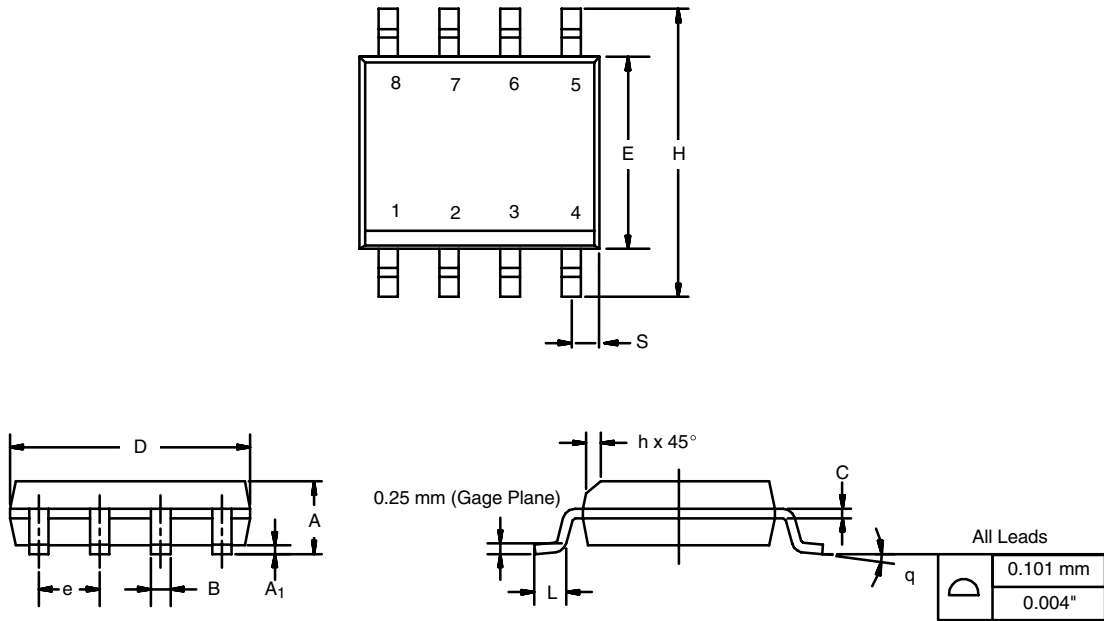


Capacitance

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SOIC (NARROW): 8-LEAD

JEDEC Part Number: MS-012



DIM	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A ₁	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°
S	0.44	0.64	0.018	0.026
ECN: C-06527-Rev. I, 11-Sep-06				
DWG: 5498				

RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads
Dimensions in Inches/(mm)

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